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INFORMATION DISCLOSURE				Filing Date			November 30, 2001					
INFORMATION DISCLOSURE STATEMENT BY APPLICANT				First Named Inventor			Tomohiko SHIBATA					
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					Confirmation No.			3908				
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EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

Date Considered:

Examiner:

ARRAULICE

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